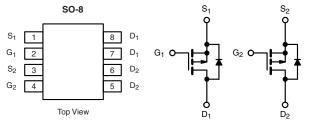
Dual P-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	- 30				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.045				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.085				
I _D (A) per leg	- 6.6				
Configuration	Dual				

FEATURES

- TrenchFET® Power MOSFET
- AEC-Q101 Qualified^c
- 100 % R_g and UIS Tested





P-Channel MOSFET P-Channel MOSFET

ORDERING INFORMATION				
Package	SO-8			
Lead (Pb)-free and Halogen-free	6F? &+' %			

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	- 30	V
Gate-Source Voltage		V _{GS}	± 20	¬
Continuous Drain Current	T _C = 25 °C	- I _D	- 6.6	A
	T _C = 125 °C		- 3.8	
Continuous Source Current (Diode Conduct	ion)	I _S	- 3	
Pulsed Drain Current ^a		I _{DM}	- 26	
Single Pulse Avalanche Current	. 0.411	I _{AS}	- 17	
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	14	mJ
Maximum Power Dissipation ^a	T _C = 25 °C	D	3.3	w
	T _C = 125 °C	P _D	1.1	
Operating Junction and Storage Temperature Range		T _J , T _{sta}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient PC	CB Mount ^b	R_{thJA}	110	°C/W		
lunction-to-Foot (Drain)		R_{thJF}	45	C/VV		

Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. When mounted on 1" square PCB (FR-4 material).
- c. Parametric verification ongoing.

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		- 30	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$		- 1.5	- 2.0	- 2.5	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		ı	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = - 30 V	ı	-	- 1	μΑ
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = -30 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$	ı	-	- 50	
		$V_{GS} = 0 V$	$V_{DS} = -30 \text{ V}, T_{J} = 175 ^{\circ}\text{C}$	ı	-	- 150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 10 V	$V_{DS} \le -5 V$	- 20	-	-	Α
		V _{GS} = - 10 V	I _D = - 4.9 A	-	0.035	0.045	Ω
Drain-Source On-State Resistance ^a	В	V _{GS} = - 10 V	I _D = - 4.9 A, T _J = 125 °C	-	-	0.066	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 4.9 A, T _J = 175 °C	-	-	0.076	
		V _{GS} = - 4.5 V	I _D = - 3.7 A	-	0.065	0.085	
Forward Transconductanceb	9 _{fs}	V _{DS} =	V _{DS} = - 15 V, I _D = - 4.9 A		9	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			ı	557	670	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = - 25 V, f = 1 MHz	ı	126	190	pF
Reverse Transfer Capacitance	C _{rss}			ı	90	115	
Total Gate Charge ^c	Qg			ı	15	22	
Gate-Source Charge ^c	Q_{gs}	V _{GS} = - 10 V	$V_{DS} = -15 \text{ V}, I_{D} = -4.9 \text{ A}$	ı	2.1		nC
Gate-Drain Charge ^c	Q_{gd}			-	3.5	-	
Gate Resistance	R_{g}	f = 1 MHz		2.60	5.26	8.50	Ω
Turn-On Delay Time ^c	t _{d(on)}			ı	3	5	
Rise Time ^c	t _r	V_{DD} = - 15 V, R_L = 6.8 Ω I_D \cong - 1 A, V_{GEN} = - 10 V, R_g = 1 Ω		-	9	14	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	20	30	
Fall Time ^c	t _f			ı	9	14	
Source-Drain Diode Ratings and Chara	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	- 26	Α
Forward Voltage	V_{SD}	I _F = - 2 A, V _{GS} = 0 V		-	- 0.8	- 1.2	V

Notes

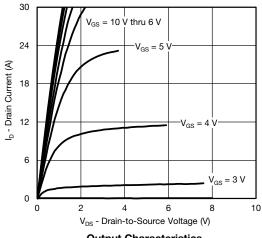
- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

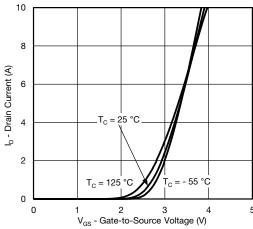




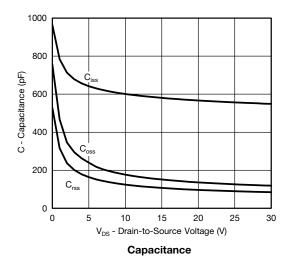
TYPICAL CHARACTERISTICS ($T_A = 25 \, ^{\circ}C$, unless otherwise noted)



Output Characteristics

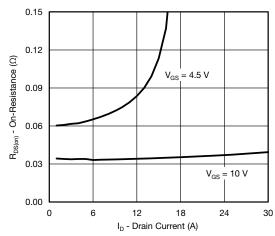


Transfer Characteristics

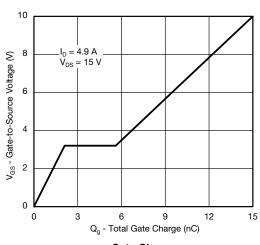


30 T_C = 25 °C 24 I_D - Drain Current (A) 18 12 6 T_C = 125 °C 55 °C 0 6 8 0 2 4 10 V_{GS} - Gate-to-Source Voltage (V)

Transfer Characteristics



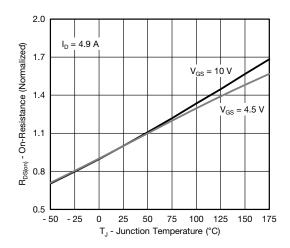
On-Resistance vs. Drain Current



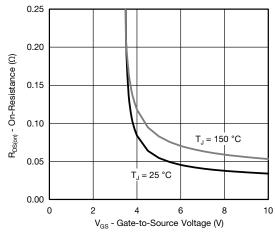
Gate Charge



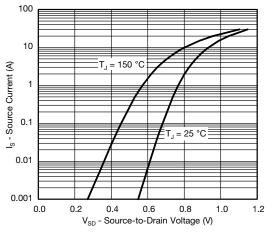
TYPICAL CHARACTERISTICS ($T_A = 25 \, ^{\circ}\text{C}$, unless otherwise noted)



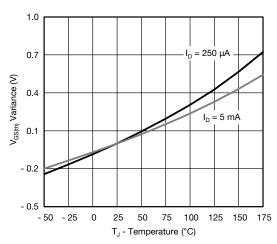
On-Resistance vs. Junction Temperature



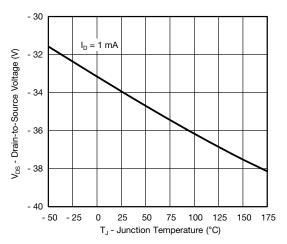
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



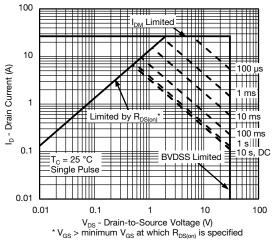
Threshold Voltage



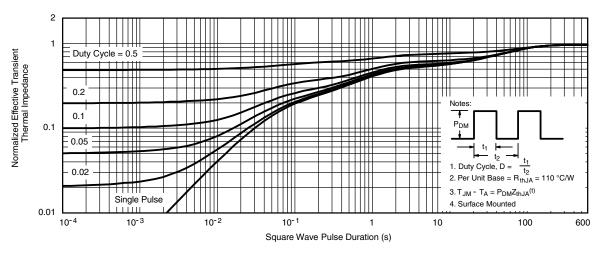
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



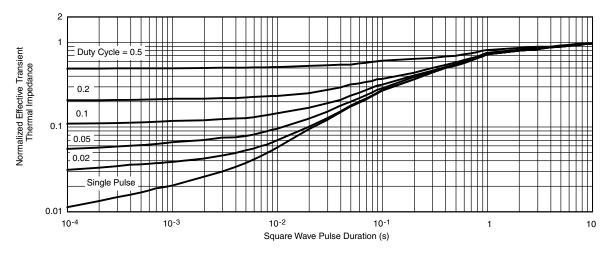
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



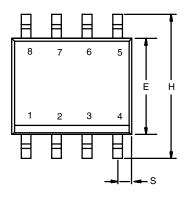
Normalized Thermal Transient Impedance, Junction-to-Foot

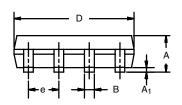
Note

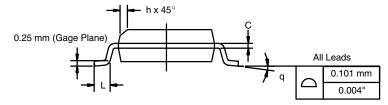
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012





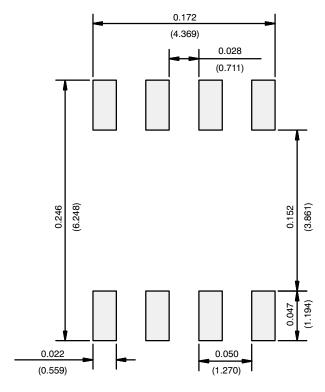


	MILLIM	IETERS	INCHES		
DIM	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
ECN: C-06527-Rev. I. 11-Sep-06					

DWG: 5498



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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